imall

Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from, Europe, America and south Asia, supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of "Quality Parts, Customers Priority, Honest Operation, and Considerate Service", our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip, ALPS, ROHM, Xilinx, Pulse, ON, Everlight and Freescale. Main products comprise IC, Modules, Potentiometer, IC Socket, Relay, Connector. Our parts cover such applications as commercial, industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



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Amp+[™] Features

- High surge current capable
- Zero reverse recovery current
- High bandwidth
- Fast, temperature-independent switching



Amp+[™] Benefits

- Unipolar rectifier • Zero switching loss
- Higher efficiency
- Smaller heat sink
- Parallel devices with thermal stability

Part # Package Marking GP2D005A120A TO-220-2L 2D005A120

PIN 10-	
PIN 20	O CASE

• Switch mode power supplies

Power factor correction

Motor drives



Maximum Rating	Symbol	Conditions	Value	Unit
		T _C =25 °C, T _j =175 °C	17	
Continuous forward current	I _F	T _C =125 °C, T _j =175 °C	10	
		T _C =150 °C, T _j =175 °C	6	Α
Surge non-repetitive forward current	1	T _C =25 °C, t _p =8.3 ms	40	A
sine halfwave	I _{F,SM}	T _C =150 °C, t _p =8.3 ms	25	
Non-repetitive peak forward current	I _{F,max}	T _C =25 °C, t _p =10 μs	100	
i ² t value	∫i²dt	T _C =25 °C, t _p =8.3 ms	7	— A ² s
1 t value	ji at	T _C =150 °C, t _p =8.3 ms	3	AS
Repetitive peak reverse voltage	V _{RRM}	T _j =25 °C	1200	V
Diode dv/dt ruggedness	dv/dt	Turn-on slew rate, repetitive	50	V/ns
Power dissipation	P _{tot}	T _C =25 °C	100	W
Operating & storage temperature	T _J , T _{storage}	Continuous	-55175	°C
Soldering temperature	T _{solder}	Wave soldering leads	260	°C
Mounting torque		M3 Screw	1	N-m

Electrical Characteristics, at Ti=25 °C, unless otherwise specified

Static Characteristics	Symbol	Conditions		Values		Unit
Static Gharacteristics	Symbol	Conditions	min.	typ.	max.	onit
DC blocking voltage	V _{DC}	I _R =0.1mA	1200	-	-	
Diode forward voltage	VF	I _F =5A, T _j =25 [°] C	-	1.60	1.80	V
Diode forward voltage	۷F	I _F =5A, T _j =175 °C	-	2.20	2.70	
Reverse current		V _R =1,200V, T _j =25 °C	-	1.0	10	
neverse current	^I R	V _R =1,200V, T _j =175 °C	-	30	300	μΑ

1200V SiC Schottky	OV SiC Schottky Diode $Amp +^{TM}$ GF		P2D005A120A			
Parameter	Symbol	Conditions		Values		Unit
Farameter	Symbol	Conditions	min.	typ.	max.	Onit
AC Characteristics						
Total capacitive charge	Q _C	V _R =1,200V, T _j =25 °C	-	22	-	nC
Switching time	t _c	di _F /dt=200 A/μs T _j =150 °C	-	-	<10	ns
Total capacitance		V _R =1 V, f=1 MHz	-	317	-	pF
	С	V _R =600V, f=1 MHz	-	19	-	
		V _R =1,200V, f=1 MHz	-	18	-	

Thermal Characteristics

	Thermal resistance, junction-case	R _{thJC}	Package (flange) mount	-	1.50	-	°C/W
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Typical Performance

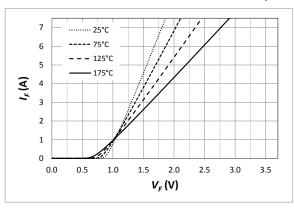




Fig. 2 Reverse Characteristics (parameterized on Tj)

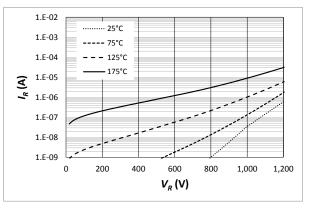
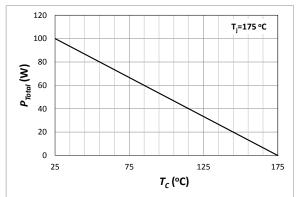
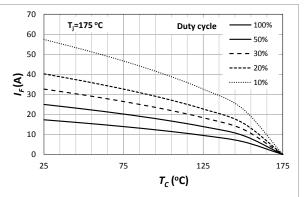


Fig. 3 Power Derating







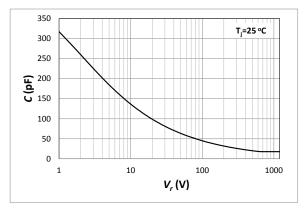
1200V SiC Schottky Diode

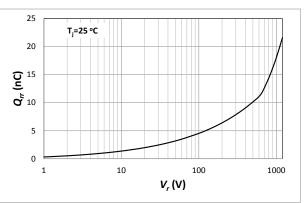
Amp+[™]

GP2D005A120A

Fig. 5 Capacitance

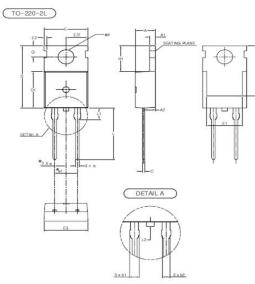
Fig. 6 Recovery Charge





Package Dimensions

Package TO-220-2L



SYMBOL	MIN	NOM	MAX		
A	4.30	4.50	4.70		
A1	1.25	1.30	1.40		
A2	2.20	2.40	2.60		
b	0.70	0.80	0.90		
b1	1.42	1.52	1.62		
b2	1.17	1.27	1.37		
с	0.45	0.50	0.60		
D	15.50	15.70	15.90		
D1	9.00	9.20	9.40		
D2	(12.70)				
E	9.00	9.20	9.40		
E1	(8.00)				
E2	(0.60)				
E3	9.70	9.90	10.10		
0	2.54 BSC				
e1	5.08 BSC				
H1	6.30	6.50	6.70		
L	12.88	13.08	13.28		
L1	(3.00)				
L2		-	0.80		
¢Ρ	3.50	3.60	3.70		
Q	2.70	2.80	2.90		

DIMENSIONS DO NOT INCLUDE PROTRUSIONS OF THE MOLD. " MARK IS THE REFERENCE " SYMBOL IS A PROTRUSION OF THE MOLD.

Note

ROHS Compliance The levels of ROHS restricted materials in this product are below the maximum concentration values (also referred to as the threshold limits) permitted for such substances, or are used in an exempted application, in accordance with EU Directive 2011/65/EC (ROHS2), as implemented March, 2013. ROHS Declarations for this product can be obtained from the Product Documentation sections of www.gptechgroup.com.

NOTE

REACh Compliance REACh substances of high concern (SVHCs) information is available for this product. Since the European Chemi- cal Agency (ECHA) has published notice of their intent to frequently revise the SVHC listing for the foreseeable future, please contact our office at GPTG Headquarters in Lake Forest, California to insure you get the most up-to-date REACh SVHC Declaration. REACh banned substance information (REACh Article 67) is also available upon request.

This product has not been designed or tested for use in, and is not intended for use in, applications implanted into the human body nor in applications in which failure of the product could lead to death, personal injury or property damage, including but not limited to equipment used in the operation of nuclear facilities, life-support machines, cardiac defibrillators or similar emergency medical equipment, aircraft navigation or communication or control systems, or air traffic control.

Global Power Technologies Group Inc., Reserves the right to make changes to the product specifications and data in this docum ent without notice.